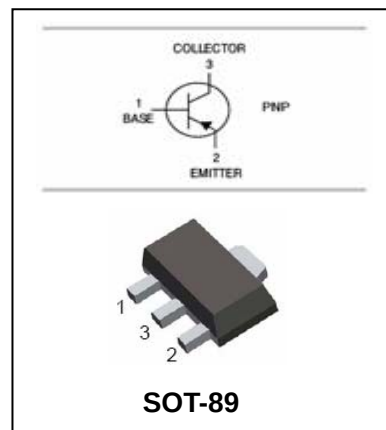


PNP SILICON EPITAXIAL TRANSISTOR

2SB806

FEATURES

- World Standard Miniature Package: SOT-89
- High Collector to Emitter Voltage:
 $V_{CEO} > -120V$



ORDERING INFORMATION

Type No.	Marking	Package Code
2SB806	KR/KQ/KP	SOT-89

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-5.0	V
I_C	Collector Current (DC)	-0.7	A
P_T	Total power dissipation	2.0	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55 to +150	°C



PNP SILICON EPITAXIAL TRANSISTOR

2SB806

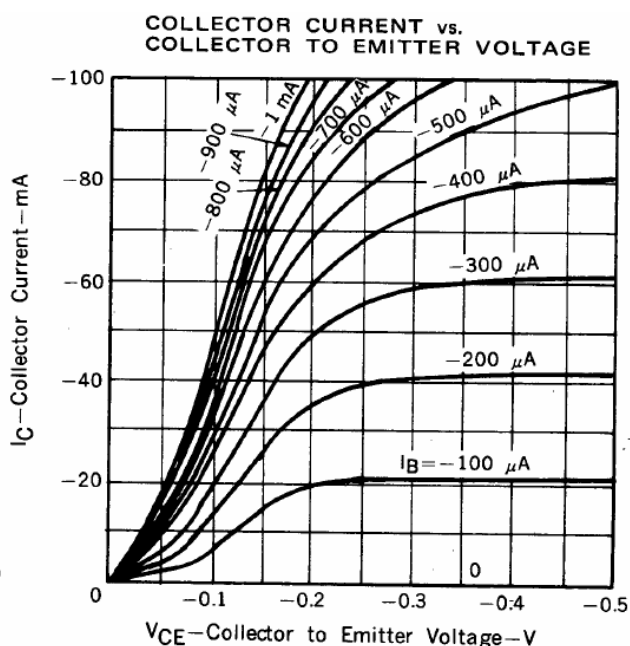
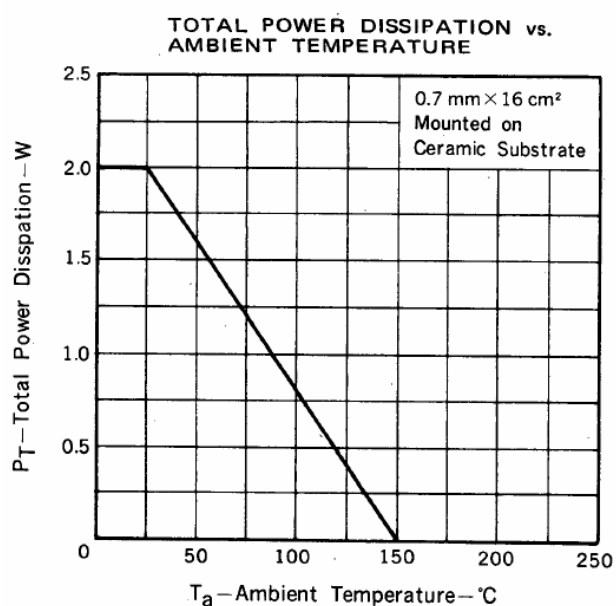
ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=-120V, I_E=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5.0V, I_C=0$			-100	nA
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C/I_B=-500mA/-50mA$		-0.4	-0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C/I_B=-500mA/-50mA$		-0.9	-1.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-10V, I_C=-10mA$	-550	-620	-650	mV
DC current gain(note)	h_{FE}	$V_{CE}=-1.0V, I_C=-5.0mA$	45	200		
		$V_{CE}=-1.0V, I_C=-100mA$	90	200	400	
Current gain bandwidth product	f_T	$V_{CE}=-10V, I_E=10mA$		75		MHz
Output Capacitance	C_{ob}	$V_{CB}=-10V, f=1MHz, I_E=0A$		14		pF

CLASSIFICATION OF h_{FE2}

RANGE	90-180	135-270	200-400
MARKING	KR	KQ	KP

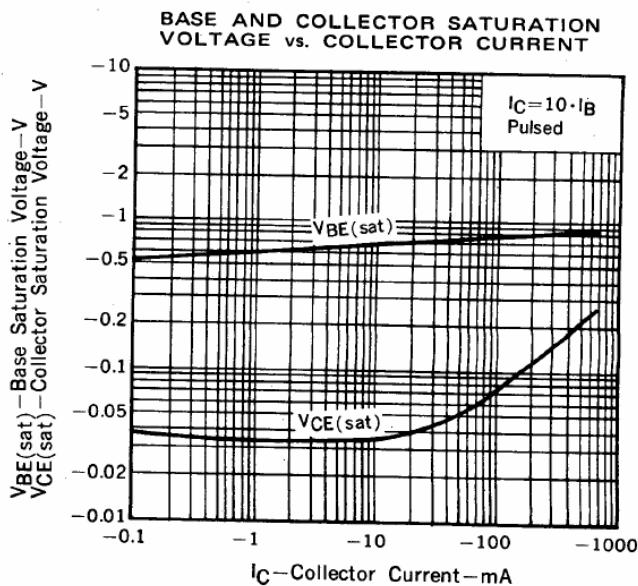
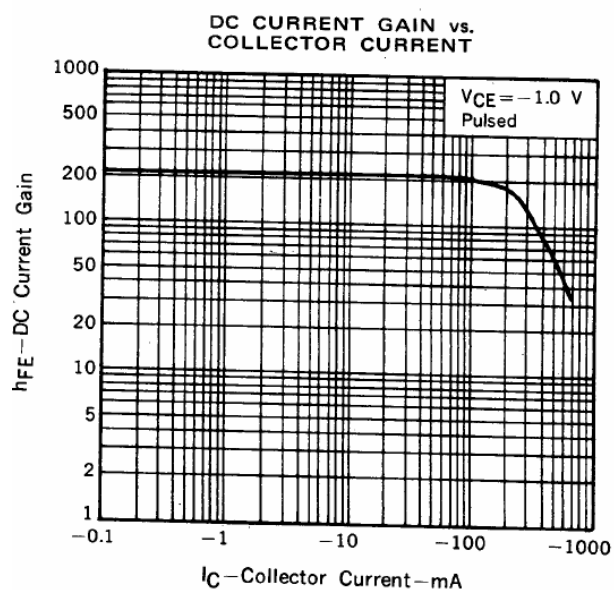
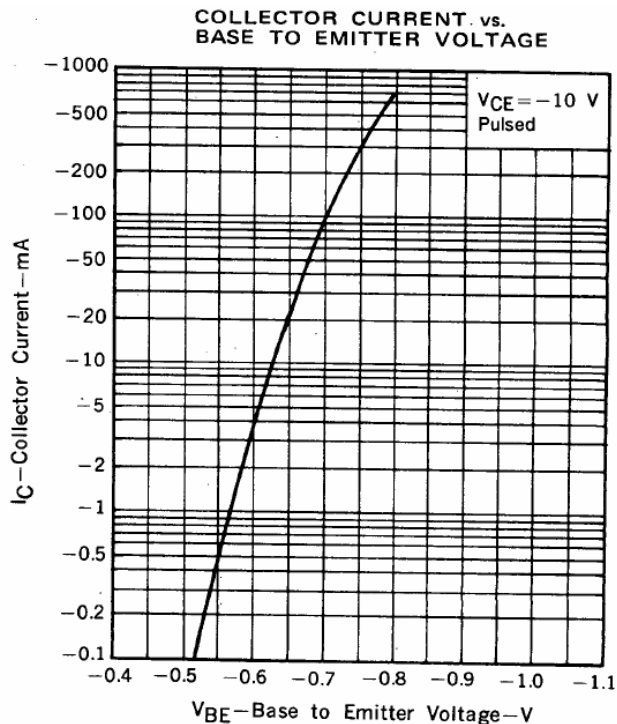
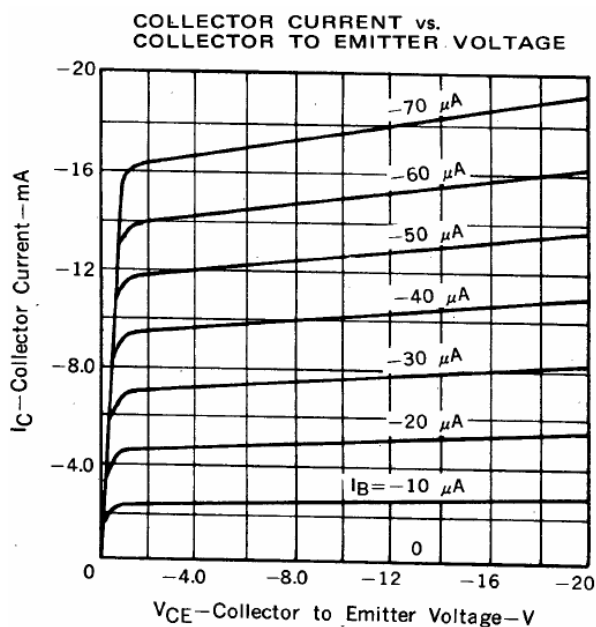
TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified





PNP SILICON EPITAXIAL TRANSISTOR

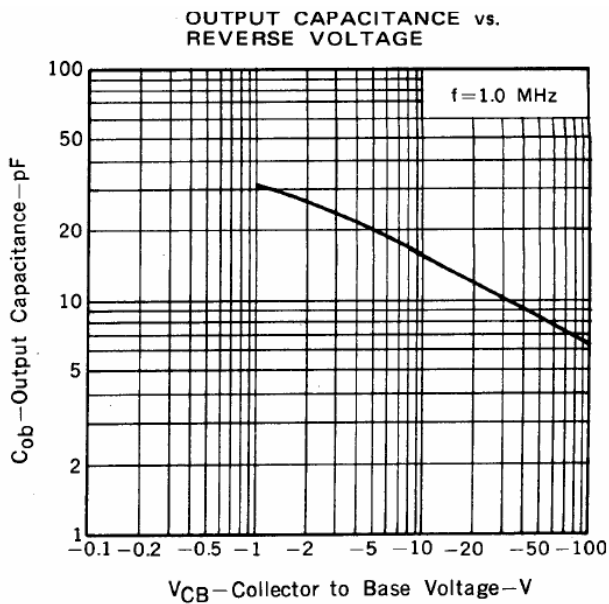
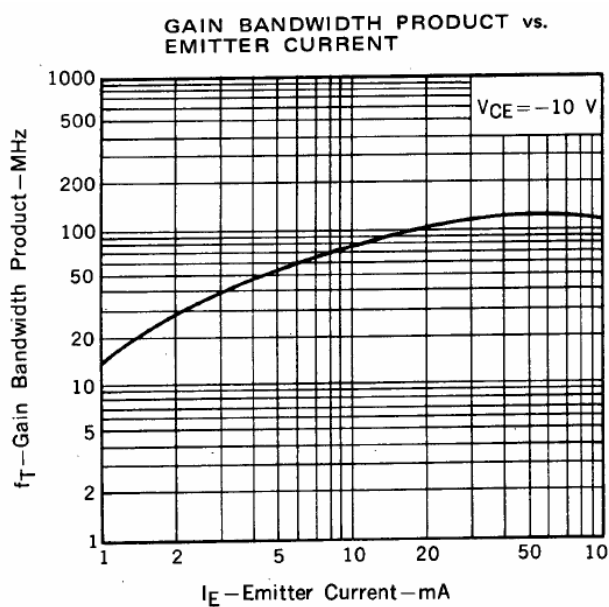
2SB806





PNP SILICON EPITAXIAL TRANSISTOR

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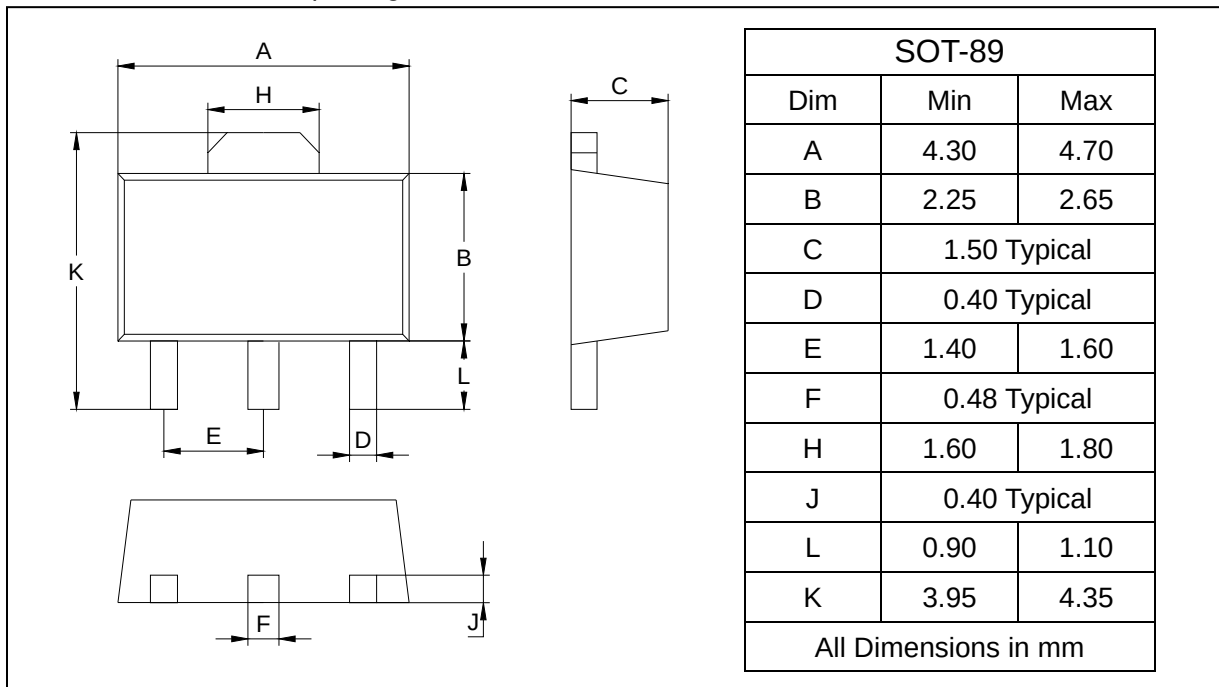
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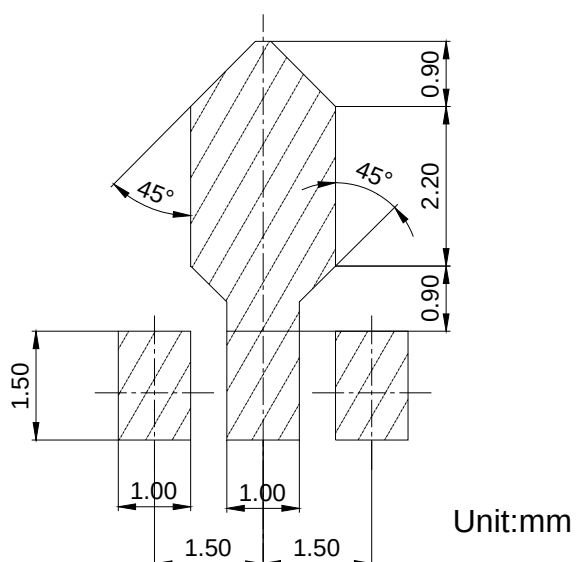
PACKAGE OUTLINE

Plastic surface mounted package

SOT-89



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SB806	SOT-89	1000/Tape&Reel